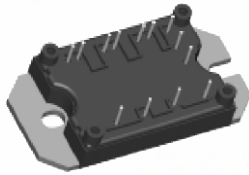



Three Phase Inverter Module in MTP Package 1200 V NPT IGBT and HEXFRED® Diodes, 15 A



MTP

PRODUCT SUMMARY	
V_{CES}	1200 V
$V_{CE(on)}$ typical at $V_{GE} = 15$ V	2.51 V
I_C at $T_C = 100$ °C	15 A
t_{sc} at $T_J = 150$ °C	> 10 μ s

FEATURES

- Generation 5 NPT 1200 V IGBT technology
- HEXFRED® diode with ultrasoft reverse recovery
- Very low conduction and switching losses
- Optional SMT thermistor (NTC)
- Aluminum oxide DBC
- Very low stray inductance design for high speed operation
- Short circuit 10 μ s
- Square RBSOA
- Operating frequencies 8 kHz to 60 kHz
- UL approved file E78996 
- Compliant to RoHS directive 2002/95/EC
- Designed and qualified for industrial level


RoHS
COMPLIANT

BENEFITS

- Optimized for inverter motor drive applications
- Low EMI, requires less snubbing
- Direct mounting to heatsink
- PCB solderable terminals
- Very low junction to case thermal resistance

ABSOLUTE MAXIMUM RATINGS				
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS
Collector to emitter voltage	V_{CES}		1200	V
Continuous collector current	I_C	$T_C = 25$ °C	30	A
		$T_C = 100$ °C	15	
Pulsed collector current	I_{CM}		60	
Peak switching current	I_{LM}		60	
Diode continuous forward current	I_F	$T_C = 100$ °C	15	
Peak diode forward current	I_{FM}		30	
Gate to emitter voltage	V_{GE}		± 20	V
RMS isolation voltage	V_{ISOL}	Any terminal to case, $t = 1$ min	2500	
Maximum power dissipation (including diode and IGBT)	P_D	$T_C = 25$ °C	187	W
		$T_C = 100$ °C	75	

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ELECTRICAL SPECIFICATIONS ($T_J = 25\text{ }^\circ\text{C}$ unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Collector to emitter breakdown voltage	$V_{(BR)CES}$	$V_{GE} = 0\text{ V}, I_C = 250\text{ }\mu\text{A}$	1200	-	-	V
Temperature coefficient of $V_{(BR)CES}$	$\Delta V_{(BR)CES}/\Delta T_J$	$V_{GE} = 0\text{ V}, I_C = 1\text{ mA}$	-	1.11	-	V/ $^\circ\text{C}$
Collector to emitter voltage	$V_{CE(on)}$	$V_{GE} = 15\text{ V}, I_C = 15\text{ A}$	-	2.51	2.70	V
		$V_{GE} = 15\text{ V}, I_C = 30\text{ A}$	-	3.36	3.66	
		$V_{GE} = 15\text{ V}, I_C = 15\text{ A}, T_J = 125\text{ }^\circ\text{C}$	-	2.94	3.16	
		$V_{GE} = 15\text{ V}, I_C = 30\text{ A}, T_J = 125\text{ }^\circ\text{C}$	-	4.12	4.46	
Gate threshold voltage	$V_{GE(th)}$	$I_C = 250\text{ }\mu\text{A}$	4	-	6	
Temperature coefficient of threshold voltage	$\Delta V_{GE(th)}/\Delta T_J$	$V_{CE} = V_{GE}, I_C = 1\text{ mA}$	-	- 10	-	mV/ $^\circ\text{C}$
Forward transconductance	g_{fe}	$V_{CE} = 25\text{ V}, I_C = 15\text{ A}$	-	12	-	S
Collector to emitter leaking current	I_{CES}	$V_{GE} = 0\text{ V}, V_{CE} = 1200\text{ V}$	-	-	250	μA
		$V_{GE} = 0\text{ V}, V_{CE} = 1200\text{ V}, T_J = 125\text{ }^\circ\text{C}$	-	-	1000	
Diode forward voltage drop	V_{FM}	$I_F = 15\text{ A}, V_{GE} = 0\text{ V}$	-	2.13	2.58	V
		$I_F = 30\text{ A}, V_{GE} = 0\text{ V}$	-	2.70	3.33	
		$I_F = 15\text{ A}, V_{GE} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$	-	2.27	2.75	
		$I_F = 30\text{ A}, V_{GE} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$	-	3.06	3.76	
Gate to emitter leakage current	I_{GES}	$V_{GE} = \pm 20\text{ V}$	-	-	± 250	nA

SWITCHING CHARACTERISTICS ($T_J = 25\text{ }^\circ\text{C}$ unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Total gate charge (turn-on)	Q_g	$I_C = 15\text{ A}$ $V_{CC} = 600\text{ V}$ $V_{GE} = 15\text{ V}$	-	98	146	nC
Gate to emitter charge (turn-on)	Q_{ge}		-	12	17	
Gate to collector charge (turn-on)	Q_{gc}		-	46	69	
Turn-on switching loss	E_{on}	$I_C = 15\text{ A}, V_{CC} = 600\text{ V}, V_{GE} = 15\text{ V}$ $R_g = 10\text{ }\Omega, L = 500\text{ }\mu\text{H}, T_J = 25\text{ }^\circ\text{C}$ Energy losses include tail and diode reverse recovery	-	0.990	1.485	mJ
Turn-off switching loss	E_{off}		-	0.827	1.241	
Total switching loss	E_{ts}		-	1.817	2.726	
Turn-on switching loss	E_{on}	$I_C = 15\text{ A}, V_{CC} = 600\text{ V}, V_{GE} = 15\text{ V}$ $R_g = 10\text{ }\Omega, L = 500\text{ }\mu\text{H}, T_J = 125\text{ }^\circ\text{C}$ Energy losses include tail and diode reverse recovery	-	1.352	2.028	mJ
Turn-off switching loss	E_{off}		-	1.138	1.707	
Total switching loss	E_{ts}		-	2.490	3.735	
Turn-on delay time	$t_{d(on)}$	$I_C = 15\text{ A}, V_{CC} = 600\text{ V}, V_{GE} = 15\text{ V}$ $L = 500\text{ }\mu\text{H}, L_S = 100\text{ nH}$ $R_g = 10\text{ }\Omega, T_J = 125\text{ }^\circ\text{C}$	-	95	143	ns
Rise time	t_r		-	18	27	
Turn-off delay time	$t_{d(off)}$		-	134	200	
Fall time	t_f		-	227	341	
Reverse BIAS safe operating area	RB SOA	$T_J = 150\text{ }^\circ\text{C}, I_C = 60\text{ A}$ $R_g = 10\text{ }\Omega, V_{GE} = 15\text{ V to }0$	Fullsquare			
Short circuit safe operating area	SC SOA	$V_{CC} = 600\text{ V}, V_{GE} = +15\text{ V to }0$ $T_J = 150\text{ }^\circ\text{C}, V_P = 1200\text{ V}, R_g = 10\text{ }\Omega$	10	-	-	μs
Input capacitance	C_{ies}	$V_{GE} = 0\text{ V}$ $V_{CC} = 30\text{ V}$ $f = 1\text{ MHz}$	-	1302	1953	pF
Output capacitance	C_{oes}		-	717	1076	
Reverse transfer capacitance	C_{res}		-	38	57	
Diode reverse recovery energy	E_{rec}	$I_C = 15\text{ A}, V_{CC} = 600\text{ V}, V_{GE} = 15\text{ V}$ $L = 500\text{ }\mu\text{H}, L_S = 100\text{ nH}$ $R_g = 10\text{ }\Omega, T_J = 125\text{ }^\circ\text{C}$	-	819	-	μJ
Diode reverse recovery time	t_{rr}		-	96	-	ns
Diode peak reverse current	I_{rr}		-	35	-	A

THERMISTOR SPECIFICATIONS (T CODE ONLY)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Resistance	R_0 ⁽¹⁾	$T_0 = 25\text{ °C}$	-	30	-	k Ω
Sensitivity index of the thermistor material	β ⁽¹⁾⁽²⁾	$T_0 = 25\text{ °C}$ $T_1 = 85\text{ °C}$	-	4000	-	K

Notes

⁽¹⁾ T_0, T_1 are thermistor's temperatures

$$\text{(2)} \quad \frac{R_0}{R_1} = \exp\left[\beta\left(\frac{1}{T_0} - \frac{1}{T_1}\right)\right]$$

THERMAL AND MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Operating junction temperature range	T_J		- 40	-	150	$^{\circ}\text{C}$
Storage temperature range	T_{Stg}		- 40	-	125	$^{\circ}\text{C}$
Junction to case	IGBT	R_{thJC}	-	-	1.1	$^{\circ}\text{C/W}$
	Diode		-	-	1.7	
	Module		-	0.50	-	
Case to sink per module	R_{thCS}	Heatsink compound thermal conductivity = 1 W/mK	-	0.1	-	$^{\circ}\text{C/W}$
Mounting torque			-	-	4	Nm
Weight			-	65	-	g

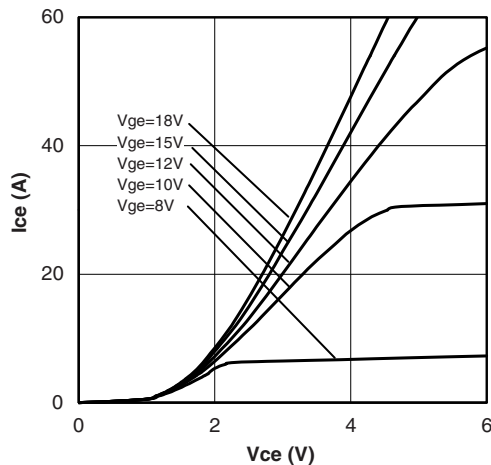


Fig. 1 - Typical Output Characteristics
 $T_J = 25\text{ °C}$

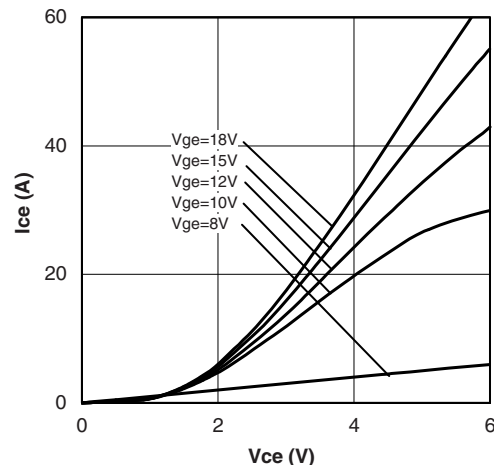


Fig. 2 - Typical Output Characteristics
 $T_J = 125\text{ °C}$

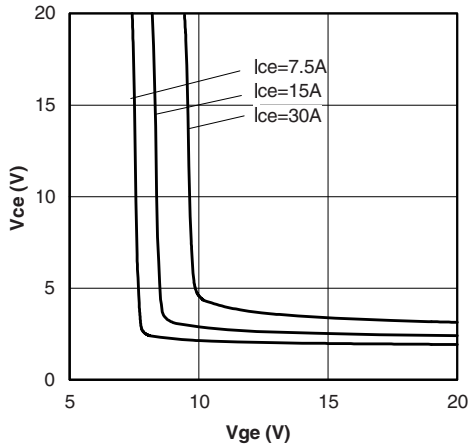


Fig. 3 - Typical V_{CE} vs. V_{GE}
 $T_J = 25\text{ }^\circ\text{C}$

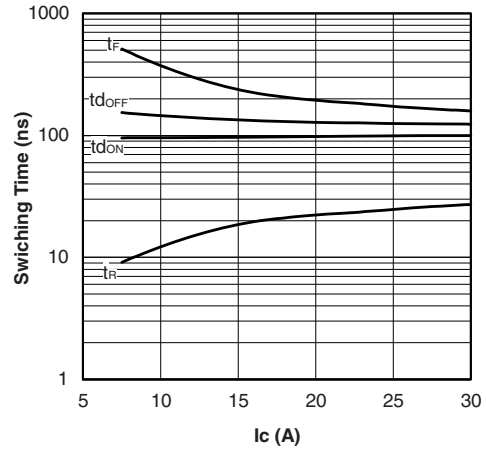


Fig. 6 - Typical Switching Time vs. I_C
 $T_J = 125\text{ }^\circ\text{C}$, $L = 500\text{ }\mu\text{H}$, $V_{CE} = 600\text{ V}$
 $R_g = 10\text{ }\Omega$; $V_{GE} = 15\text{ V}$

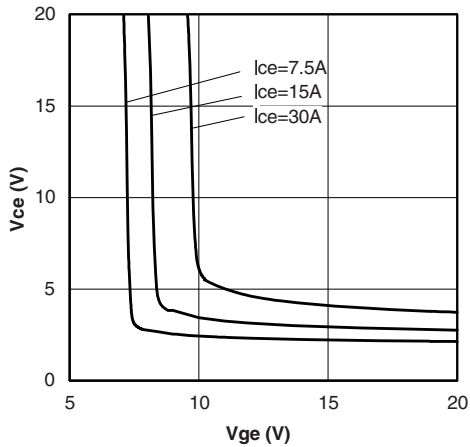


Fig. 4 - Typical V_{CE} vs. V_{GE}
 $T_J = 125\text{ }^\circ\text{C}$

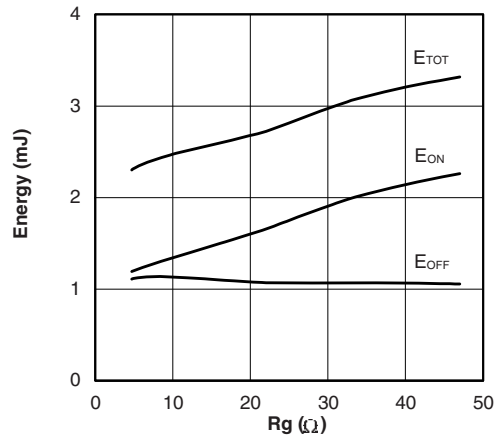


Fig. 7 - Typical Energy Loss vs. R_g
 $T_J = 125\text{ }^\circ\text{C}$, $L = 500\text{ }\mu\text{H}$, $V_{CE} = 600\text{ V}$
 $I_C = 15\text{ A}$; $V_{GE} = 15\text{ V}$

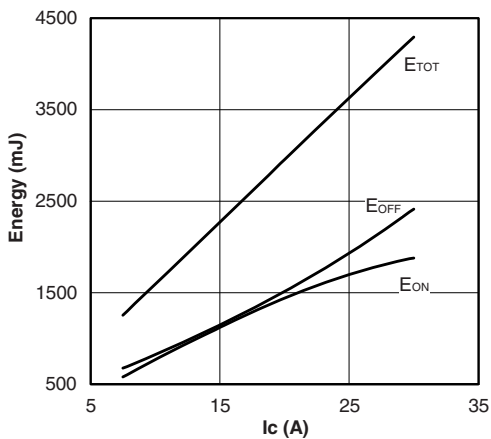


Fig. 5 - Typical Energy Loss vs. I_C
 $T_J = 125\text{ }^\circ\text{C}$, $L = 500\text{ }\mu\text{H}$, $V_{CE} = 600\text{ V}$
 $R_g = 10\text{ }\Omega$; $V_{GE} = 15\text{ V}$

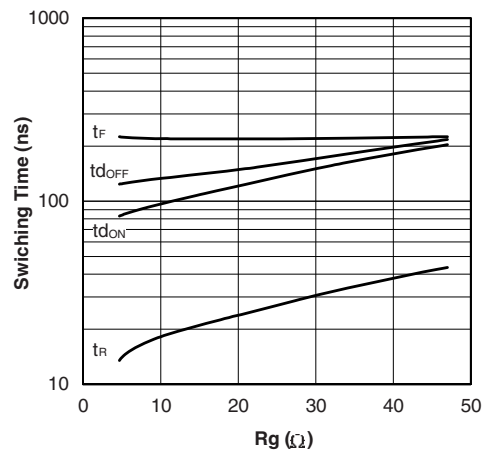


Fig. 8 - Typical Switching Time vs. R_g
 $T_J = 125\text{ }^\circ\text{C}$, $L = 500\text{ }\mu\text{H}$, $V_{CE} = 600\text{ V}$
 $I_C = 15\text{ A}$; $V_{GE} = 15\text{ V}$

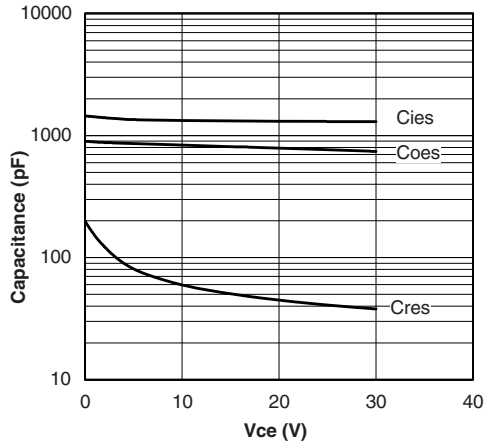


Fig. 9 - Typical Capacitance vs. V_{CE}
 $V_{GE} = 0 \text{ V}$; $f = 1 \text{ MHz}$

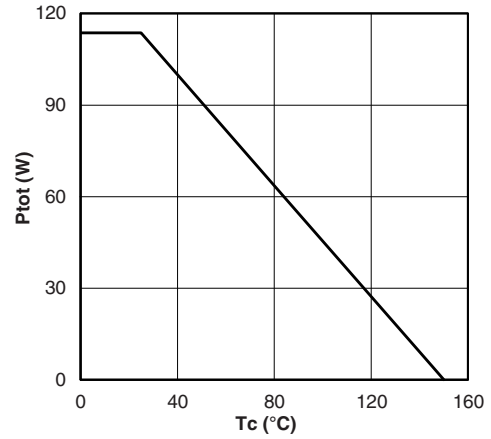


Fig. 12 - Power Dissipation vs. Case Temperature
 (IGBT only)

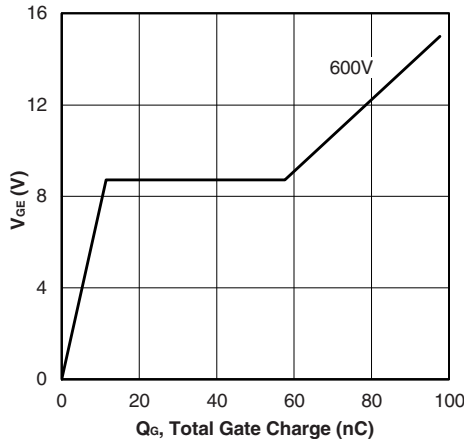


Fig. 10 - Typical Gate Charge vs. V_{GE}
 $I_{CE} = 15 \text{ A}$

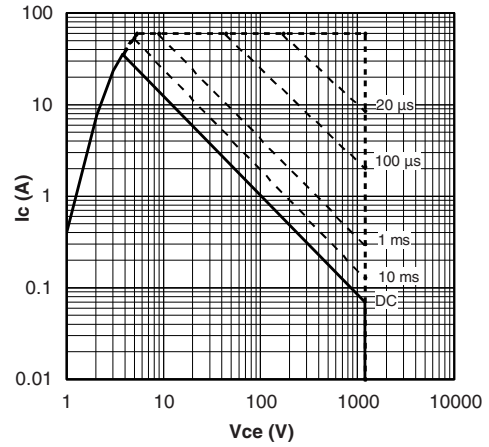


Fig. 13 - Forward SOA
 $T_C = 25 \text{ }^\circ\text{C}$, $T_J \leq 150 \text{ }^\circ\text{C}$

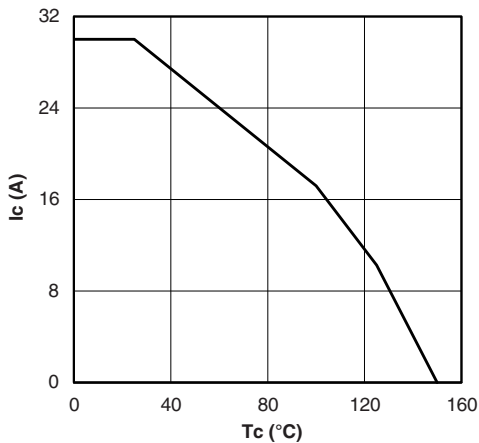


Fig. 11 - Maximum DC Collector Current vs.
 Case Temperature

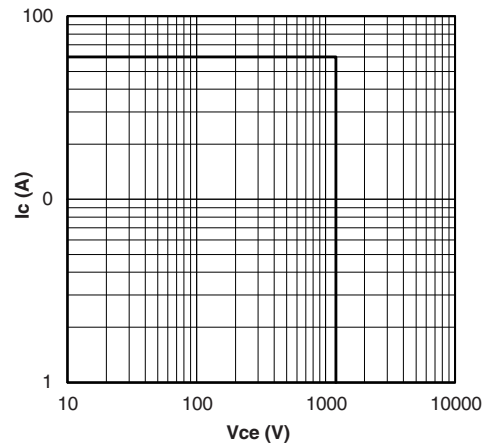


Fig. 14 - Reverse BIAS SOA
 $T_J = 150 \text{ }^\circ\text{C}$, $V_{GE} = 15 \text{ V}$

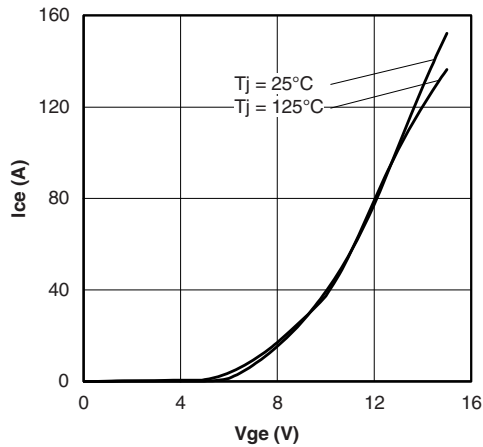


Fig. 15 - Typical Transfer Characteristics
 $V_{CE} = 50 \text{ V}$; $t_p = 10 \mu\text{s}$

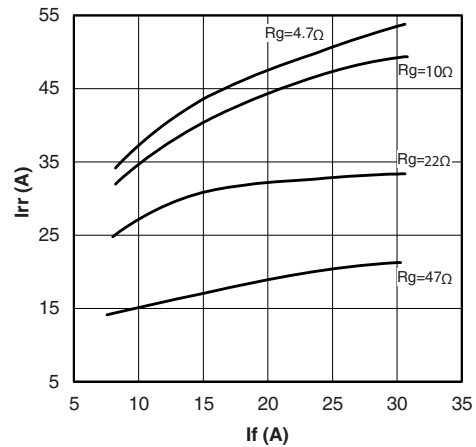


Fig. 17 - Typical Diode I_{rr} vs. I_F
 $T_J = 125^\circ\text{C}$

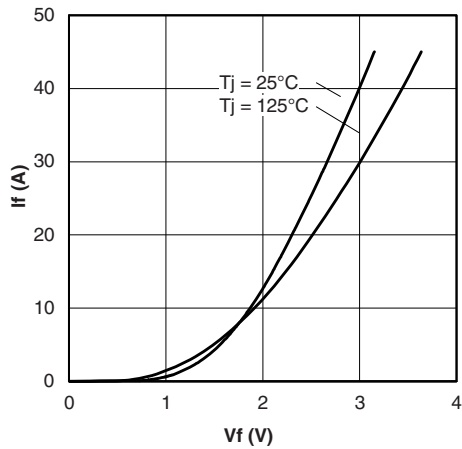


Fig. 16 - Typical Diode Forward Characteristics
 $t_p = 80 \mu\text{s}$

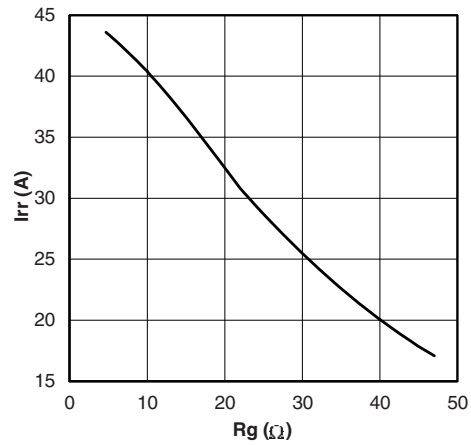


Fig. 18 - Typical Diode I_{rr} vs. R_g
 $T_J = 125^\circ\text{C}$; $I_F = 10 \text{ A}$

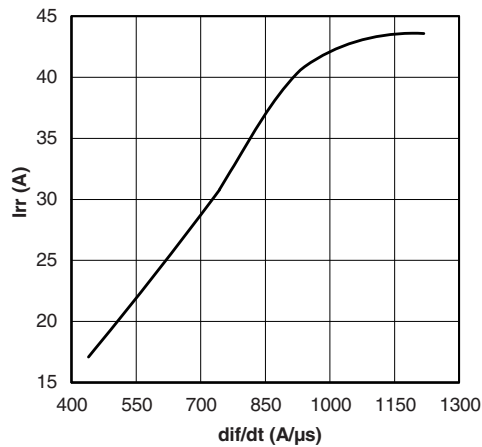


Fig. 19 - Typical Diode I_{rr} vs. dI_F/dt ; $V_{CC} = 600 \text{ V}$;
 $V_{GE} = 15 \text{ V}$; $I_{CE} = 10 \text{ A}$, $T_J = 125^\circ\text{C}$

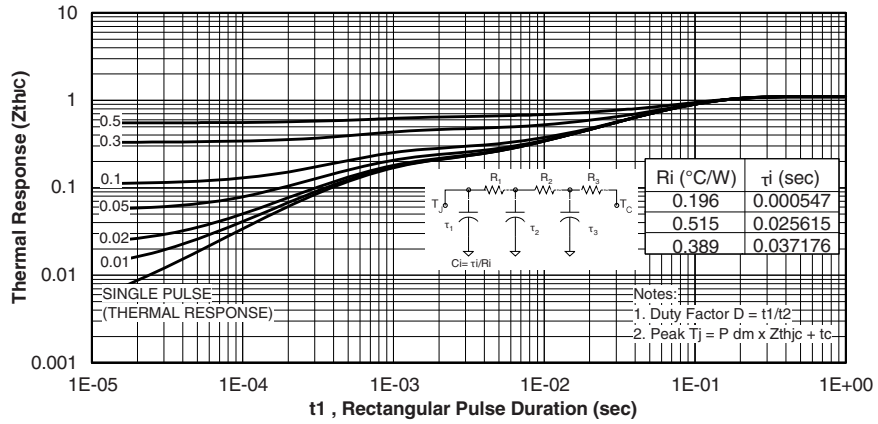


Fig. 20 - Maximum Transient Thermal Impedance, Junction to Case (IGBT)

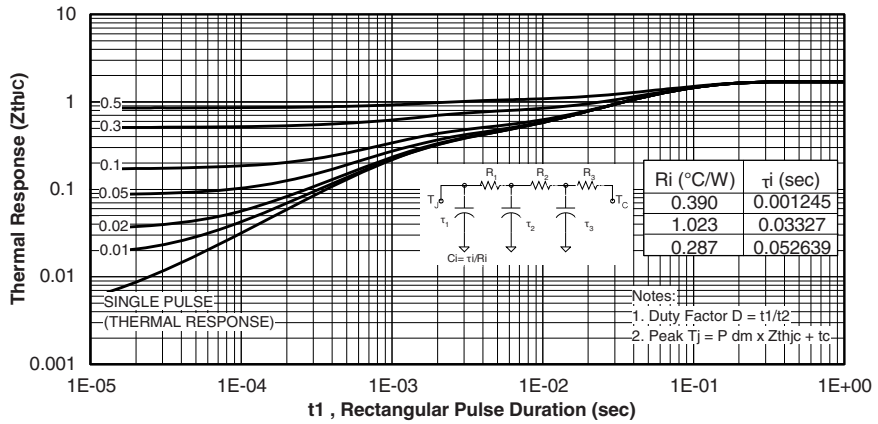


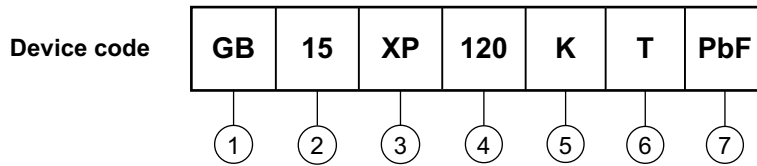
Fig. 21 - Maximum Transient Thermal Impedance, Junction to Case (Diode)

GB15XP120KTPbF



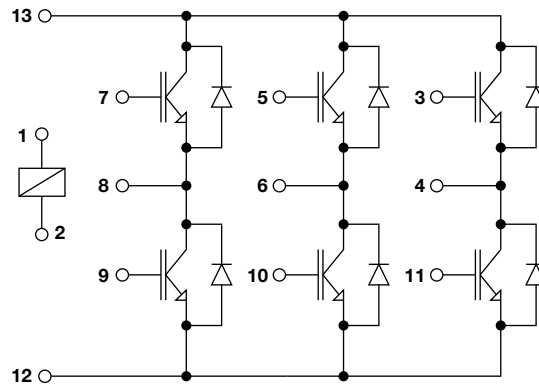
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1200 V NPT IGBT and HEXFRED® Diodes, 15 A

ORDERING INFORMATION TABLE



- 1** - IGBT module
- 2** - Nominal current rating (15 = 15 A)
- 3** - Circuit configuration (XP = Three phase inverter)
- 4** - Voltage code (120 = 1200 V)
- 5** - Speed/type (K = Ultrafast IGBT/inverter motor drive application)
- 6** - Special option:
 - None = No special option
 - T = Thermistor
- 7** - PbF = Lead (Pb)-free

CIRCUIT CONFIGURATION



LINKS TO RELATED DOCUMENTS	
Dimensions	www.vishay.com/doc?95175

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